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TRX_024_06

24 GHz Highly Integrated IQ Transceiver (Silicon Germanium Technology)

Preliminary Data Sheet

| | | | |
|------------------------|---------------------|------------------------------------|------------------|
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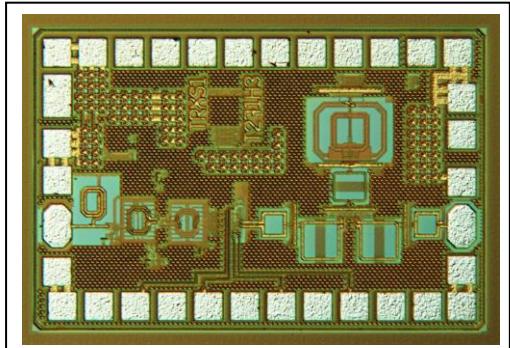
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1 Features

- Radar transceiver for 24 GHz ISM band
- Single supply voltage of 3.3V
- Fully ESD protected device
- Low power consumption 300mW
- Integrated low phase noise Push-Push VCO
- Transmitter with power control in four steps
- Receiver with homodyne quadrature mixer
- Low-noise-amplifier (LNA) with gain control
- Single ended TX output
- Single ended RX input
- QFN-20 leadless plastic package 3x3mm²
- Pb-free (RoHS compliant) package
- IC is available as bare die as well



1.1 Overview

The IC is an integrated transceiver circuit for the 24 GHz ISM-band in the frequency range 24.0GHz – 24.25GHz. It includes a low-noise-amplifier (LNA) with gain control, quadrature mixers, poly-phase filter, Voltage Controlled Oscillator with digital band switching and divide by 32 circuit. The receiver can be powered down if PWR_RX pin is supplied with 0V. The gain of the receiver can be digitally controlled by Vct pin, Vct = 3.3 V sets the receiver in high gain modus, Vct = 0 V sets the receiver in low gain modus. The output power of the transmitter can be controlled by pwr0 and pwr1 inputs. The IC is fabricated in SiGe BiCMOS technology by using the bipolar part and the CMOS part.

1.2 Applications

The main use of the TRX transceiver IC in wireless communication systems and in radar systems for the ISM-band from 24.0 GHz to 24.25 GHz and for UWB-applications between 23GHz and 29GHz.

2 Block Diagram

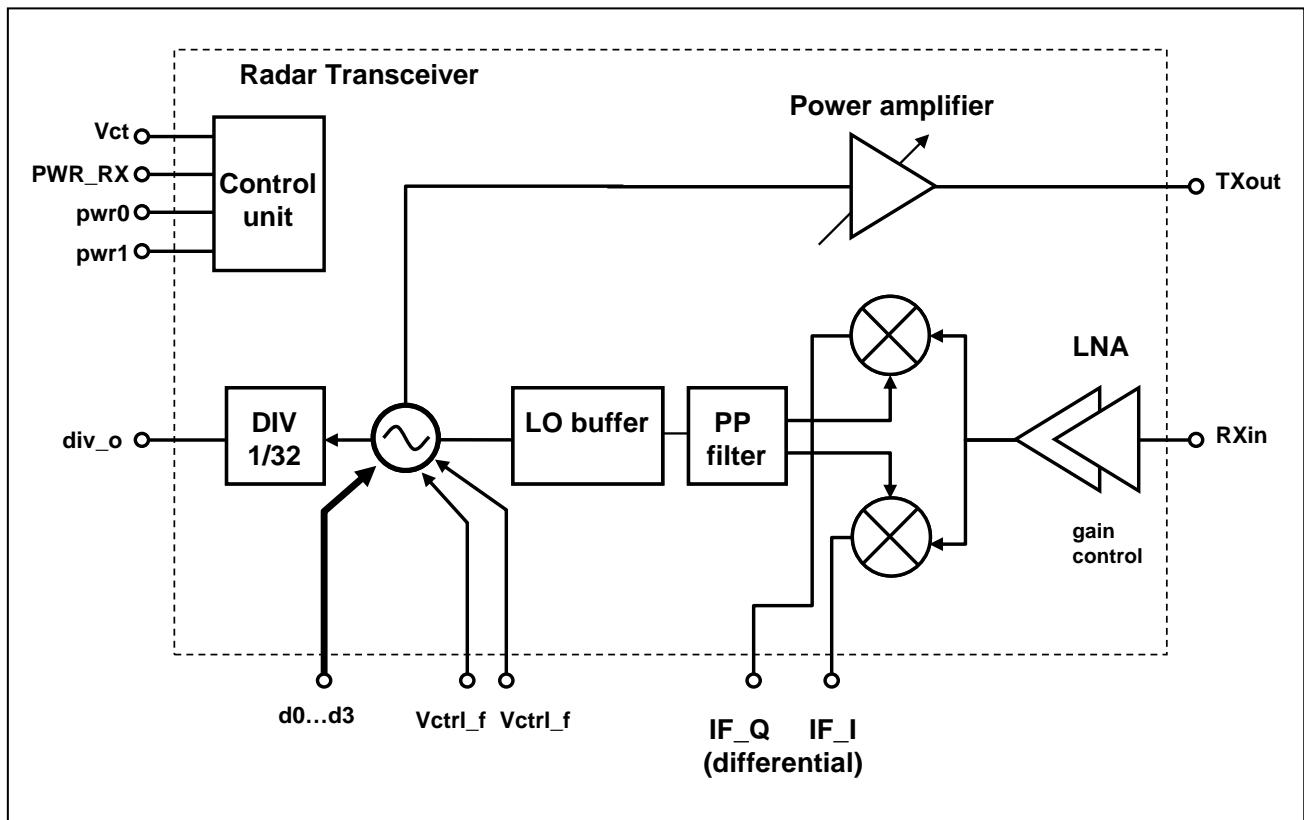


Figure 1 TRX_024_06 Block Diagram

3 Electrical Characteristics

3.1 Absolute Maximum Ratings

$T_A = 25^\circ\text{C}$ unless otherwise noted

Table 1 Absolute Maximum Ratings

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Remarks / Condition |
|------------------------------|-------------|------|------|-------|------------------|---|
| Supply Voltage | V_{cc} | +3.0 | +3.3 | +3.6 | V | to GND |
| DC voltage at RF Pins | V_{DCRF} | 0 | - | 0.002 | V | IC provides low ohmic circuit to GND for TXout and RXin |
| Operating temperature range | T_{use} | -40 | - | +85 | $^\circ\text{C}$ | Industrial |
| Storage temperature range | T_{store} | -65 | - | +150 | $^\circ\text{C}$ | |
| Junction temperature | T_{junc} | | | +150 | $^\circ\text{C}$ | |
| Input power into pin RFin | P_{IN} | - | - | 0 | dBm | |
| DC voltage at control inputs | V_{ctl} | 0 | - | 3.3 | V | d0, d1, d2, d3, Vctrl |
| Supply current consumption | I_{cc} | - | 89 | 103 | mA | @ 3.3V Vcc |

Attempted operation outside the absolute maximum ratings of the part may cause permanent damage to the part. Actual performance of the IC is only guaranteed within the operational specifications, not at absolute maximum ratings.

3.2 Thermal Resistance

Table 2 Thermal Resistance

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Remarks / Condition |
|---|------------|------|------|------|------|-----------------------|
| Thermal resistance from junction to soldering point | R_{thJS} | - | - | 50 | K/W | see application notes |

3.3 ESD Integrity

Table 3 ESD Integrity

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Remarks / Condition |
|---|-----------|------|------|------|------|---------------------------|
| ESD robustness of TXout, RFin | V_{ESD} | 1,3 | - | 2 | kV | All RF-Pins ¹⁾ |
| ESD robustness of all low frequency and DC pins | V_{ESD} | 1,3 | | 2 | kV | |

1) According to ESDA/JEDEC Joint Standard for Electrostatic Discharge Sensitivity Testing, Human Body Model (HBM) Component Level, ANSI/ESDA/JEDEC JS-001-2011

4 RF Characteristics

4.1 Transmitter Section TX

$T_A = -40^\circ\text{C} + 85^\circ\text{C}$ unless otherwise noted

Table 4 Typical Characteristics Transmitter Section

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Remarks / Condition |
|-----------------------------------|---|-------|--|-------|----------|--|
| Transmitter frequency range | f_{TX} | 23.20 | | 26.30 | GHz | |
| Tuning voltage VCO | V_{ctrl} | 0.0 | - | 3.0 | V | |
| Tuning slope VCO | $\Delta f_{\text{TX}}/\Delta V_{\text{ctrl}}$ | | 220 MHz/V | | | |
| Number adjustable frequency bands | | - | 16 | - | - | d0 – d3: VCO band switching, each input with internal pull-down resistor (120 kOhm) |
| Pushing VCO | $\Delta f_{\text{TX}}/\Delta V_{\text{CC}}$ | | 135 | | MHz/V | @ $f = 24, 15$ GHz |
| Phase Noise | P_N | - | -102 | -105 | dBc/Hz | @ 1MHz offset |
| Output impedance | Z_{TXout} | | 50 | | Ω | |
| Transmitter output power | P_{TX} | 2.5 | 4 | 6 | dBm | |
| Adjustable range output power | $P_{\text{TX_ADJ}}$ | 0 | | 4 | dBm | Power Amplifier Gain control (pwr1 pin) $1 - P_{\text{out_max}}$ $0 - P_{\text{out_max}} - 4$ dBm |
| Divider division ratio | $D_{\text{div_o}}$ | - | 32 | - | - | - |
| Divider output power | $P_{\text{div_o}}$ | -9 | -8.5 | -8 | dBm | Divider output loaded with 50Ω , $\square \square$ DC coupled, external decoupling capacitor required (min 100pF) |
| Divider output frequency range | $f_{\text{div_o}}$ | 725 | | 821 | MHz | |
| Spurios | | | -40dBm @ $F_{\text{Tx}} - F_{\text{div}}$ -43dBm @ $F_{\text{Tx}} + F_{\text{div}}$ | | GHz | |
| Harmonics | | | -46dBm @12GHz -40dBm @48GHz | | GHz | |

4.2 Receiver Section RX

$T_A = -40^\circ\text{C} + 85^\circ\text{C}$ unless otherwise noted

Table 5 Typical Characteristics Receiver Section

| Parameter | Symbol | Min. | Typ. | Max. | Unit | Remarks / Condition |
|-----------------------------------|------------|-------|---------------|-------|----------|---|
| Receiver frequency range | f_{RX} | 23.30 | - | 26.20 | GHz | |
| Receiver input impedance | Z_{RXIN} | | 50 | | Ω | |
| Number adjustable gain modes | | | 2 | | | Adjustable LNA gain control (internal pull-up resistor) |
| Gain high gain mode | | | | 18 | dB | $V_{ct}=3.3\text{ V}$ |
| Gain low gain mode | | | | 11 | dB | $V_{ct}=0\text{ V}$ |
| IF frequency range | f_{IF} | 0 | - | 200 | MHz | |
| IF output impedance | | | 470 \square | | Ω | differential |
| IQ amplitude balance | | | 1.0 | | dB | |
| IQ phase balance | | | 10 | | deg | |
| Noise figure (DSB) high gain mode | | | 4 | | dB | Simulated (Double side band @ $f_{IF}=1\text{MHz}$) |
| Noise figure (DSB) low gain mode | | | 6 | - | dB | Simulated |
| Input Compression Point | | -20 | - | -13 | dBm | |

5 Application Circuit

5.1 Chip Outline

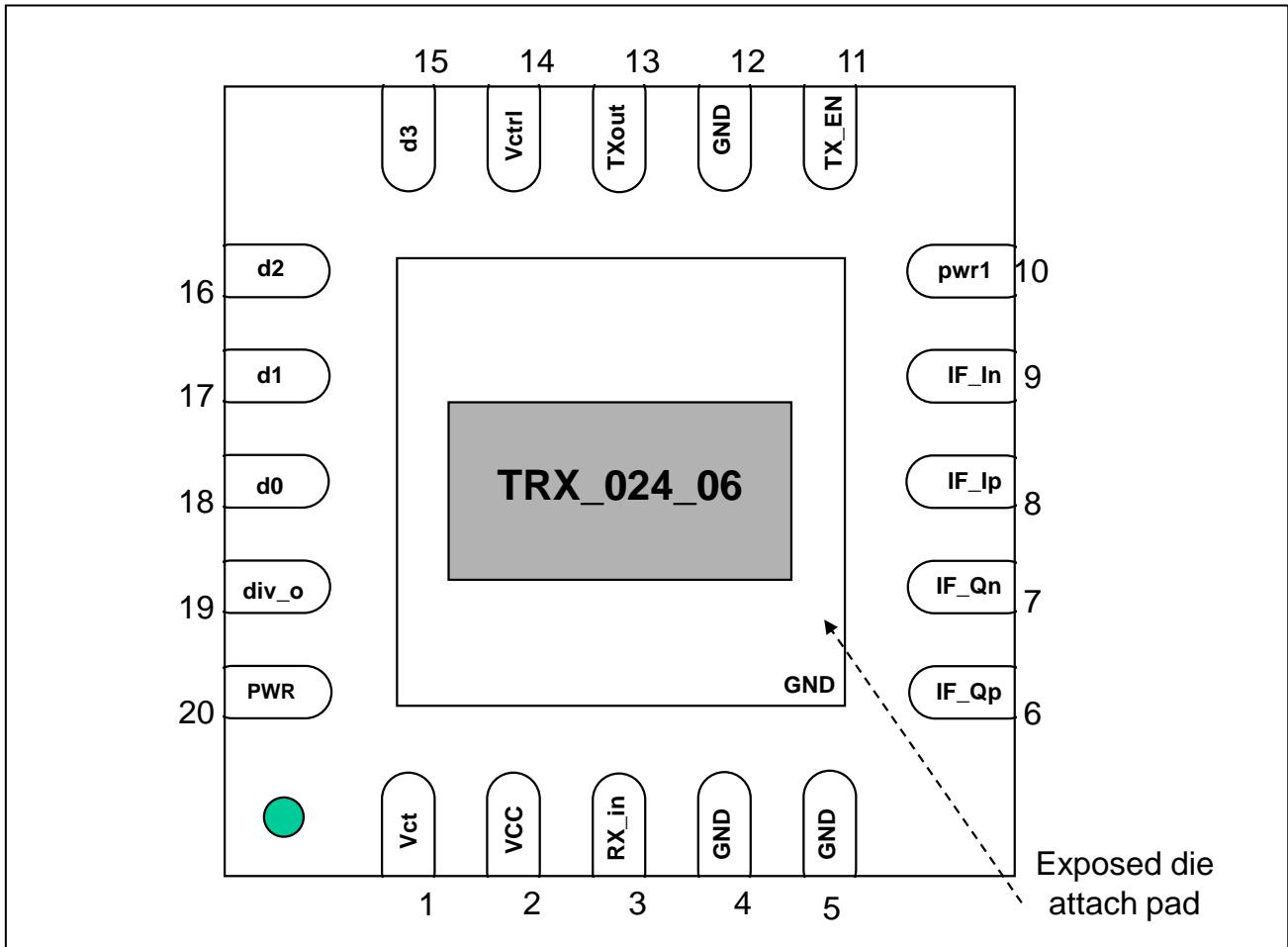


Figure 2 TRX_024_06 Chip outline (top view)

5.2 Pin Description

Table 6 Pin Description

| Pin No. | Name | Description |
|---------|-------|--|
| 1 | Vct | LNA gain control (internal pull-up resistor) |
| 2 | vcc | Supply voltage |
| 3 | RXin | RF input, 50Ω |
| 4 | GND | Ground |
| 5 | GND | Ground |
| 6 | IF_Qp | IF Outputs, DC coupled, external AC coupling capacitors required |
| 7 | IF_Qn | |
| 8 | IF_Ip | |
| 9 | IF_In | |
| 10 | pwr1 | Power Amplifier Gain control (internal pull-up resistors) 1 – P_{out_max} 0 – $P_{out_max} - 4$ dB |

| | | |
|----|-------|---|
| 11 | TX_EN | TX enable, high active (internal pull-up resistor) |
| 12 | GND | Ground |
| 13 | TXout | Transmitter output, 50Ω |
| 14 | Vctrl | VCO tuning |
| 15 | d3 | VCO band switching, each input with internal pull-down resistor (120 kOhm) |
| 16 | d2 | |
| 17 | d1 | |
| 18 | d0 | |
| 19 | div_o | Divider output, 50Ω, DC coupled, external decoupling capacitor required (min 100pF) |
| 20 | PWR | Divider Enable (internal pull-up resistor) |
| 21 | GND | Die attach pad to ground |

5.3 Application Circuit Schematic

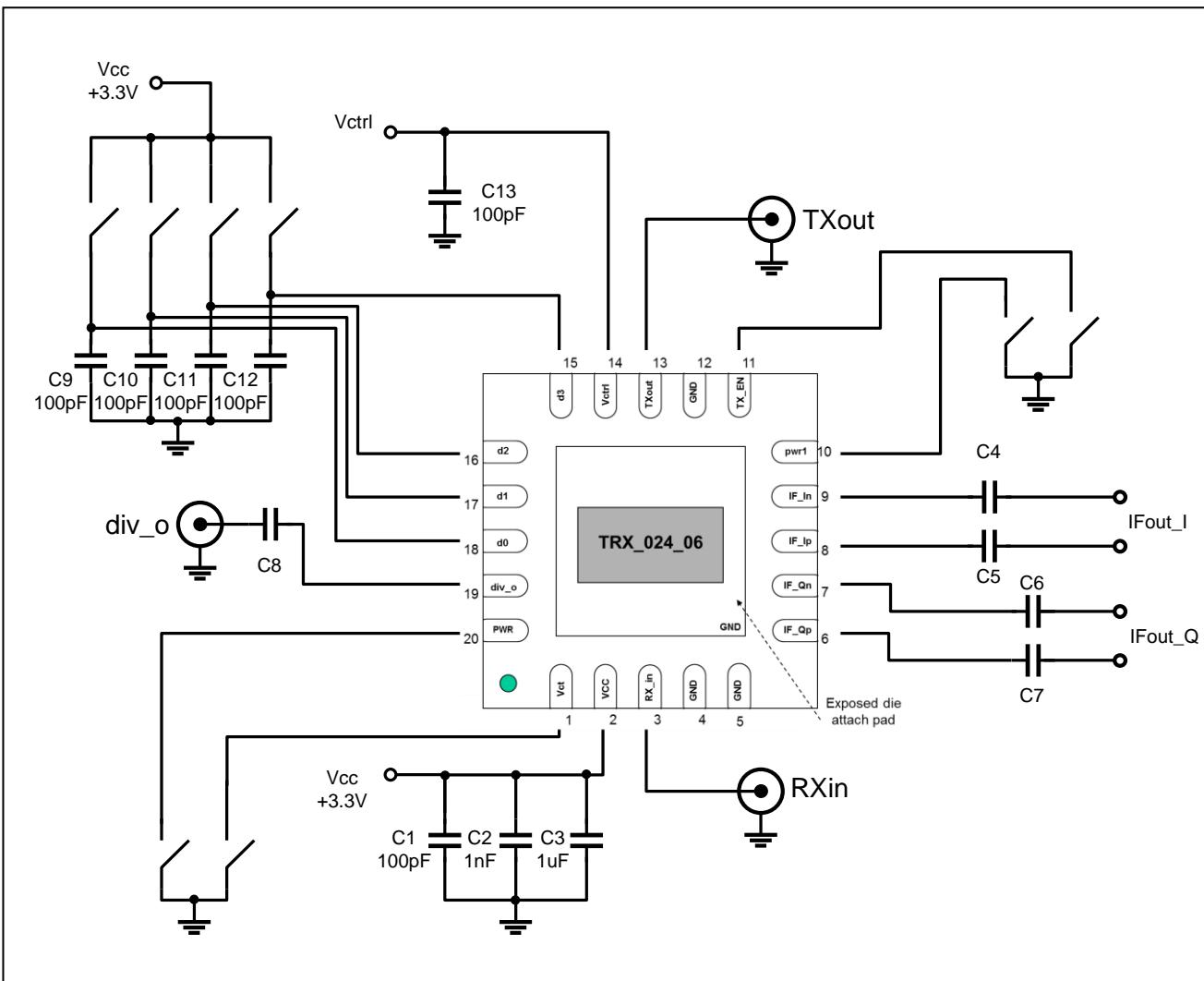


Figure 3 TRX_024_06 Application Circuit (Top view)

5.4 Evaluation Board

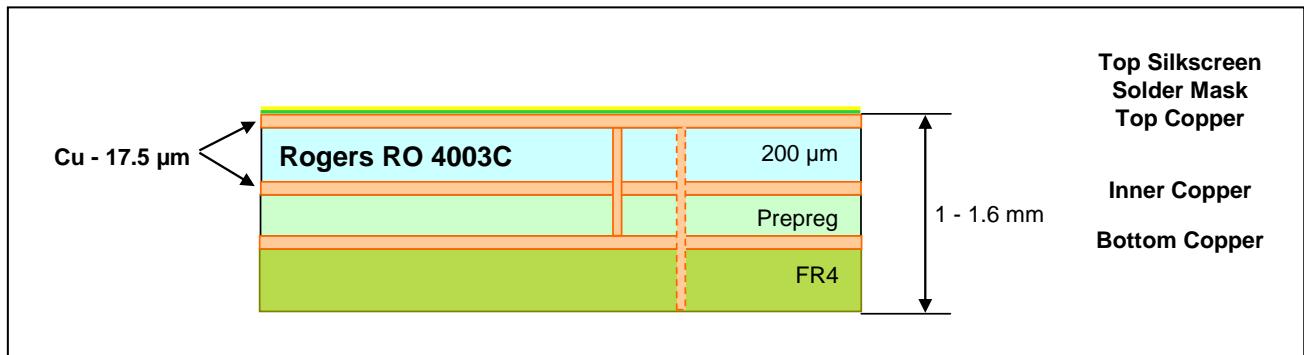


Figure 4 TRX_024_06 Evaluation board stack-up

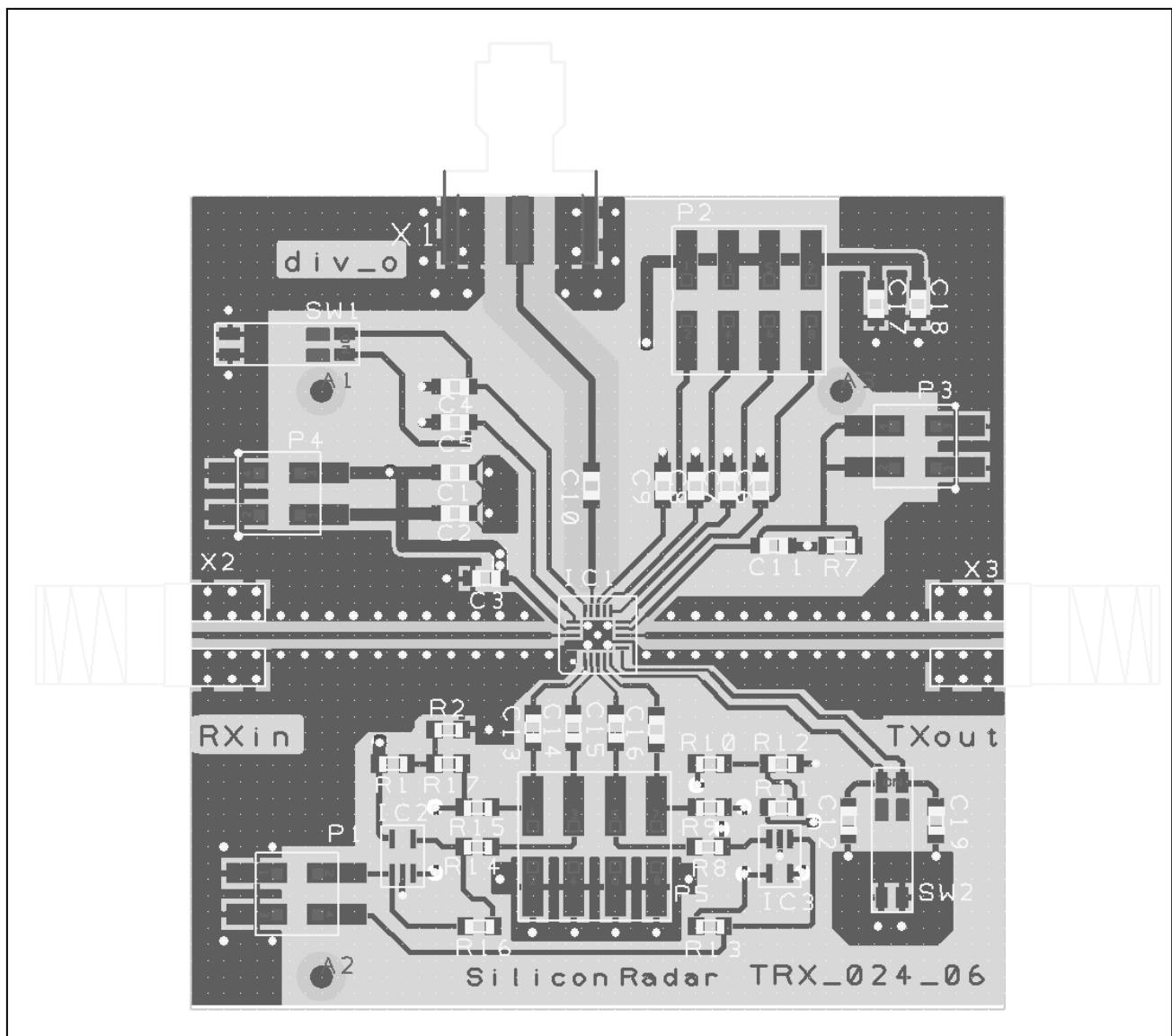
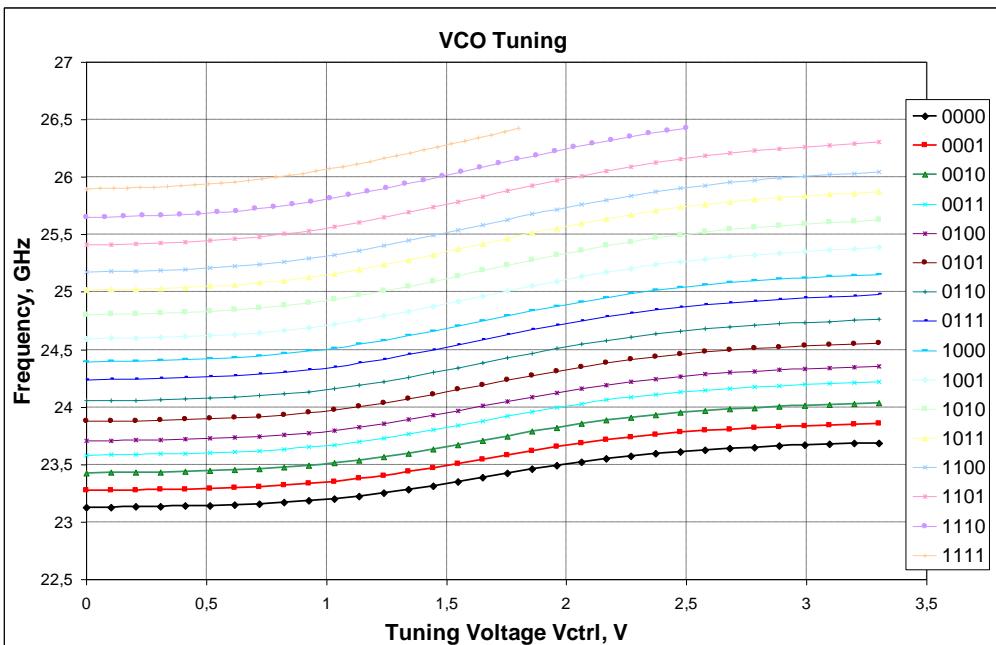


Figure 5 TRX_024_06 Evaluation Board Layout (Top view) including via holes

6 Measurement Results



Frequency bands of integrated oscillator

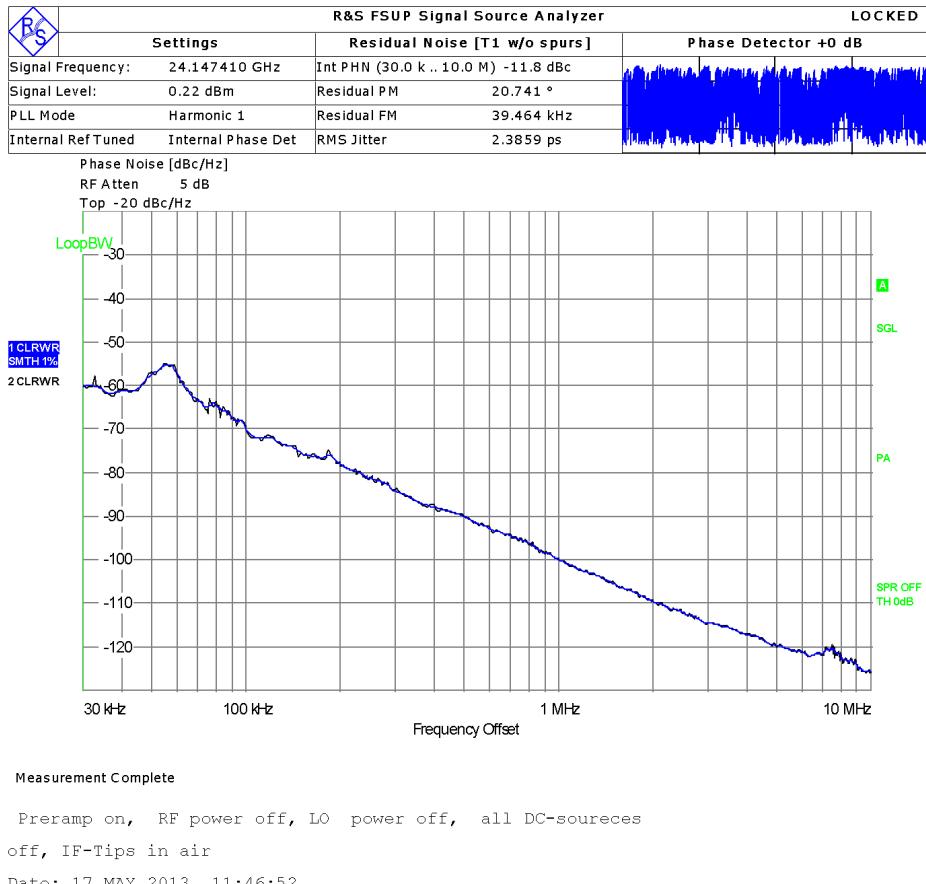
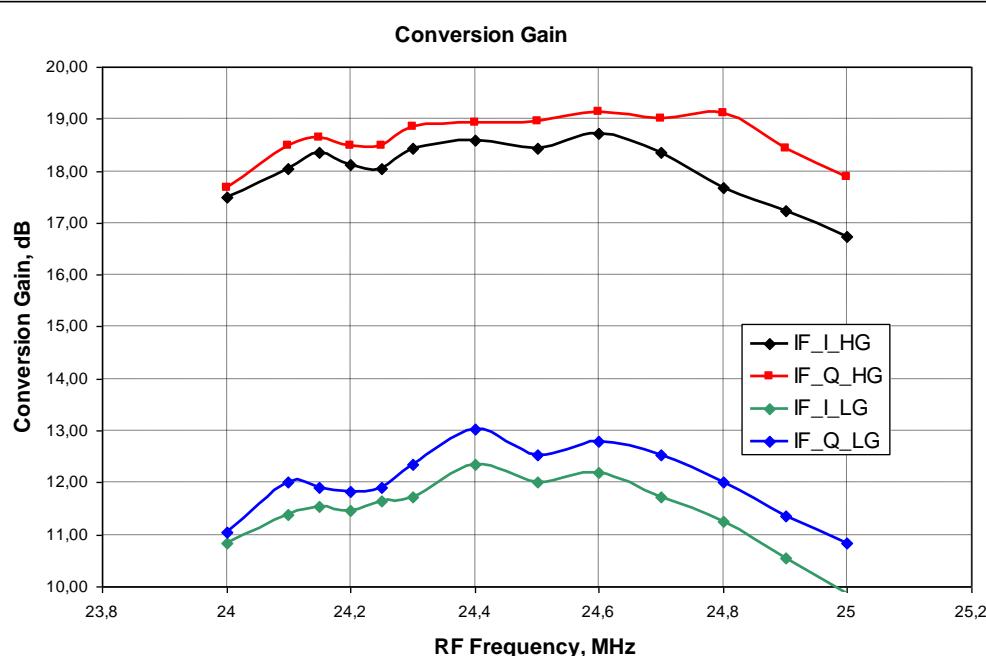
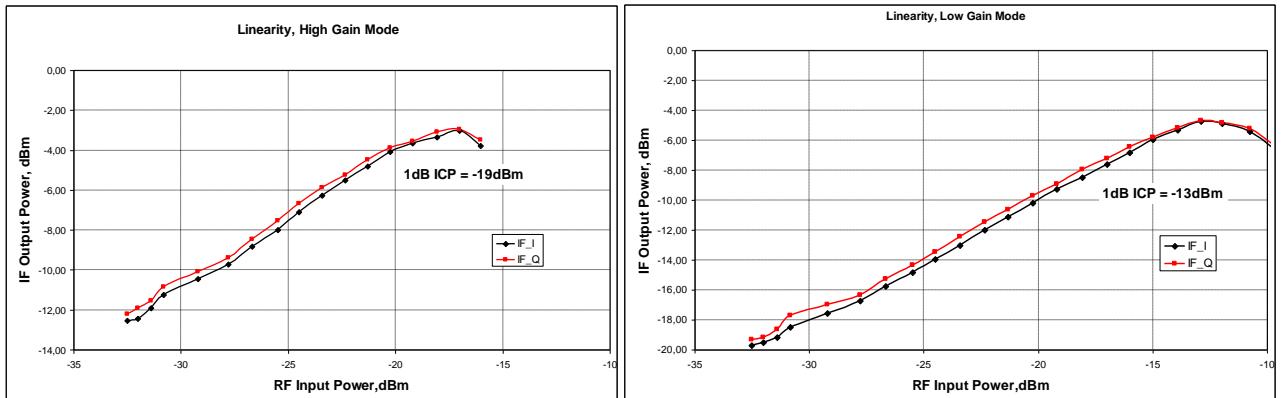


Figure 6 TRX_024_06 Measurement results



Measured conversion gain of the receiver in High-Gain and Low-Gain modus



Measured linearity of the receiver in High- and Low-Gain modus

Figure 7 TRX_024_06 Measurement results

7 Physical Characteristics

7.1 Mechanical Data QFN

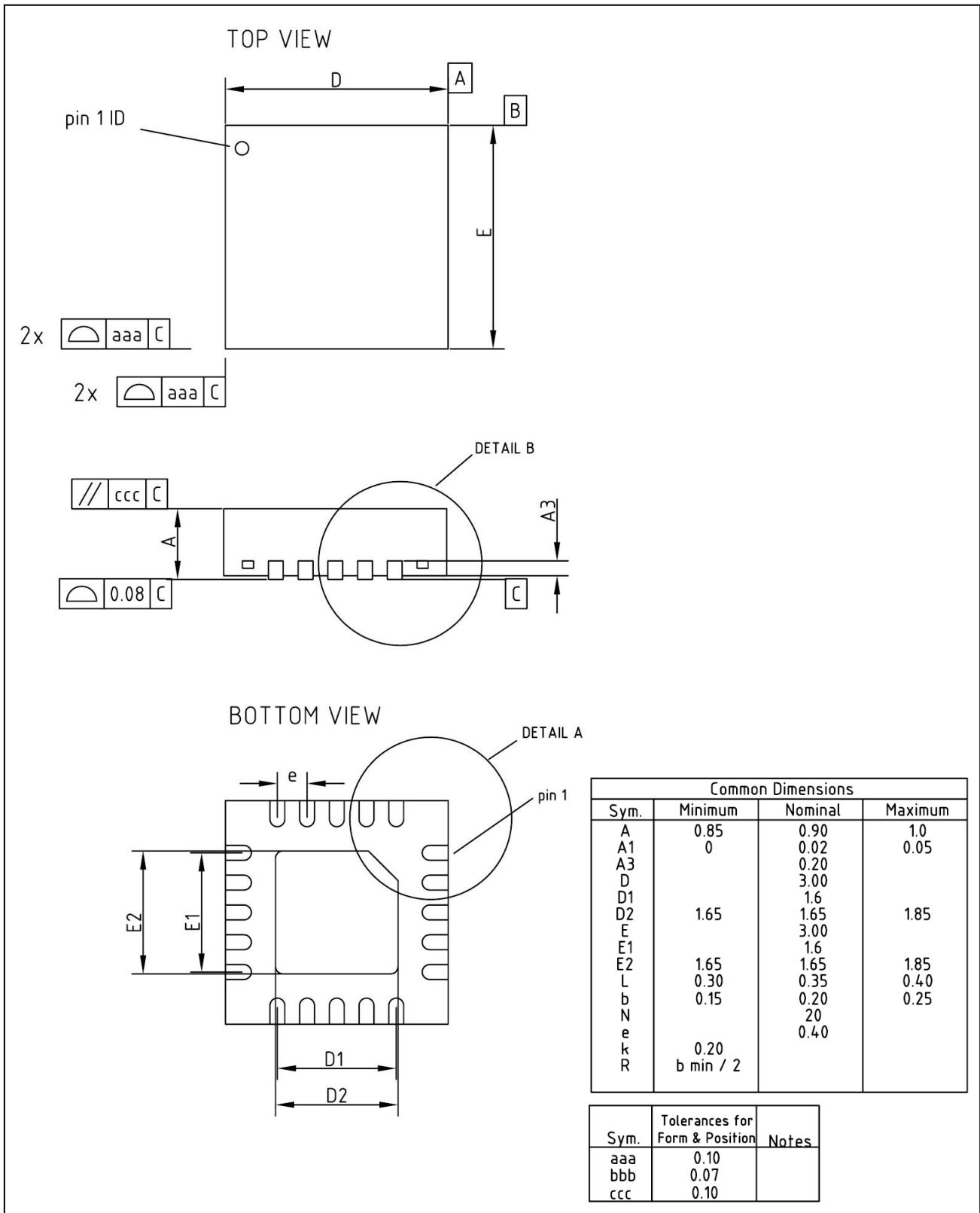


Figure 8 Mechanical data QFN 20Lead 3x3mm 0.4 pitch

7.2 Mechanical Data QFN

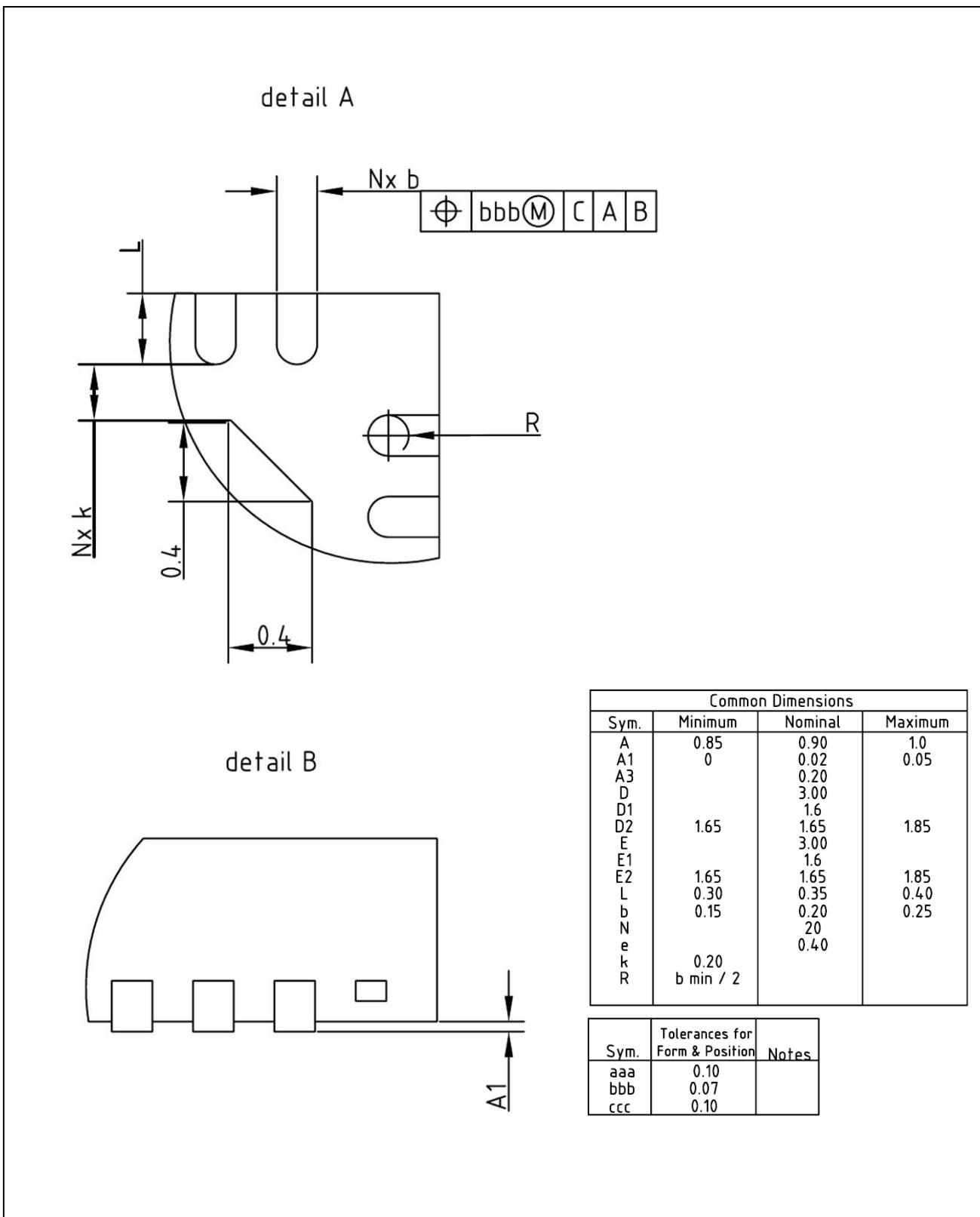


Figure 9 Mechanical data details QFN 20Lead 3x3mm 0.4 pitch

7.3 Package Footprint

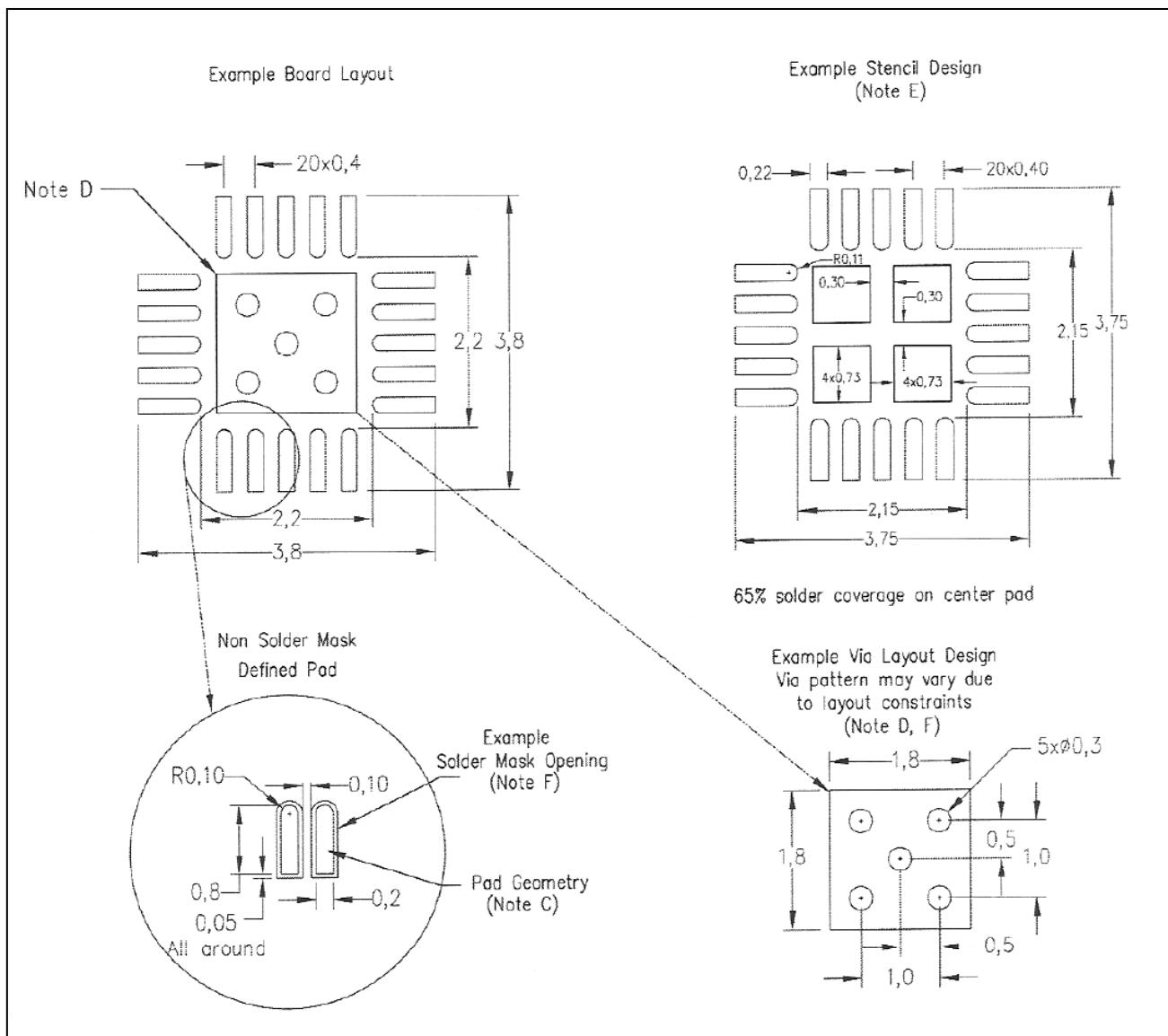


Figure 10 TRX_024_06 Package Footprint and Example Stencil Design

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